

MOSFETs Silicon N-channel MOS (U-MOSX-H)

TPM2R408QM

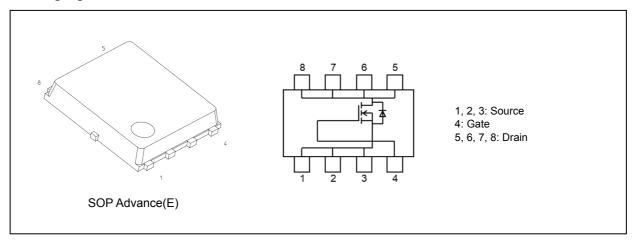
1. Applications

- High-Efficiency DC-DC Converters
- · Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) High-speed switching
- (2) Low gate charge: $Q_{SW} = 28 \text{ nC (typ.)}$
- (3) Small output charge: Qoss = 90 nC (typ.)
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 1.9 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 80 \text{ V)}$
- (6) Enhancement mode: $V_{th} = 2.5 \text{ to } 3.5 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA)}$

3. Packaging and Internal Circuit



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Rev.1.0



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	80	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)	(T _c = 25 °C)	(Note 1), (Note 2)	I _D	205	Α
Drain current (DC)		(Note 1), (Note 3)	I_D	23	
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I _{DP}	500	
Power dissipation	$(T_c = 25 ^{\circ}C)$		P_D	220	W
Power dissipation		(Note 3)	P_D	3	
Single-pulse avalanche energy		(Note 4)	E _{AS}	223	mJ
Single-pulse avalanche current		(Note 4)	I _{AS}	50	Α
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note: This product is not designed for radiation resistance or cosmic ray resistance, and these natural environmental factors may affect reliability.

In addition, radiation from the constituent materials of the product also becomes a natural environmental factor, which may affect reliability.

5. Thermal Characteristics

Characteristics			Symbol	Max	Unit
Channel-to-case thermal resistance	$(T_c = 25 ^{\circ}C)$		R _{th(ch-c)}	0.68	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 3)	R _{th(ch-a)}	50	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: This is the maximum rated current when the case temperature is maintained at 25°C.

The case temperature indicates the entire bottom side.

Note 3: Device mounted on a glass-epoxy board, Figure 5.1

Note 4: V_{DD} = 40 V, T_{ch} = 25 °C (initial), L = 110 $\mu H,\ I_{AS}$ = 50 A

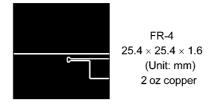


Fig. 5.1 Device Mounted on a Glass-Epoxy

Board

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	80		_	٧
Drain-source breakdown voltage (Note 5)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	60	_	_	
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.5	_	3.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 6 V, I _D = 50 A	_	2.5	3.5	mΩ
		V _{GS} = 10 V, I _D = 50 A	_	1.9	2.4	

Note 5: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 40 V, V _{GS} = 0 V, f = 1 MHz	_	5870	8300	pF
Reverse transfer capacitance	C _{rss}		_	60	116	
Output capacitance	C _{oss}		_	1340	_	
Gate resistance	r _g	_	_	1.9	2.9	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	18.4	_	ns
Switching time (turn-on time)	t _{on}		_	38	_	
Switching time (fall time)	t _f		_	34	_	
Switching time (turn-off time)	t _{off}		_	138	_	

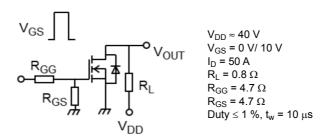


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Q_g	$V_{DD} \approx 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$	_	87	_	nC
gate-drain)		$V_{DD} \approx 40 \text{ V}, V_{GS} = 6 \text{ V}, I_D = 50 \text{ A}$	_	55	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$	_	23	_	
Gate-drain charge	Q_{gd}		_	19	_	
Gate switch charge	Q_SW		_	28	_	
Output charge	Q _{oss}	V _{DS} = 40 V, V _{GS} = 0 V, f = 1 MHz	_	90	_	



6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 6)	I _{DRP}	(t = 100 μs)	_	_	500	Α
Diode forward voltage	V_{DSF}	I _{DR} = 120 A, V _{GS} = 0 V	_	_	-1.2	V
Reverse recovery time	t _{rr}	I_{DR} = 30 A, V_{GS} = 0 V,	_	57	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	74	_	nC

Note 6: Ensure that the channel temperature does not exceed 175 °C.

7. Marking

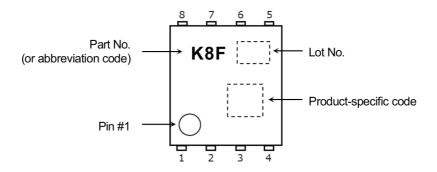


Fig. 7.1 Marking



8. Characteristics Curves (Note)

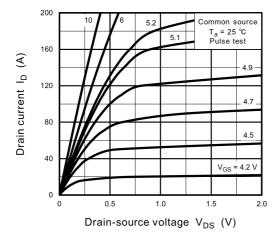


Fig. 8.1 I_D - V_{DS}

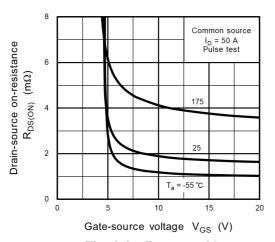


Fig. 8.3 R_{DS(ON)} - V_{GS}

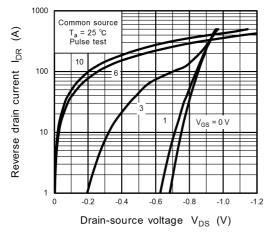


Fig. 8.5 IDR - VDS

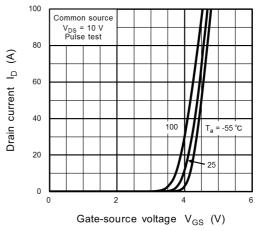


Fig. 8.2 I_D - V_{GS}

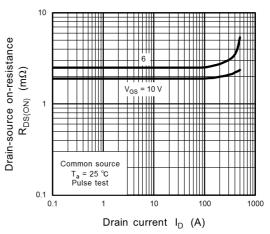


Fig. 8.4 R_{DS(ON)} - I_D

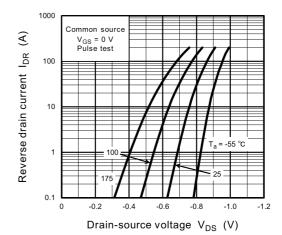


Fig. 8.6 IDR - VDS



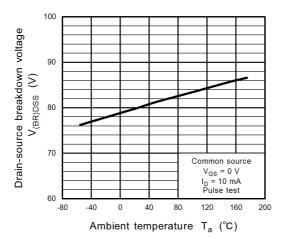


Fig. 8.7 V_{(BR)DSS} - T_a

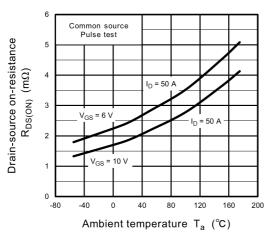


Fig. 8.9 R_{DS(ON)} - T_a

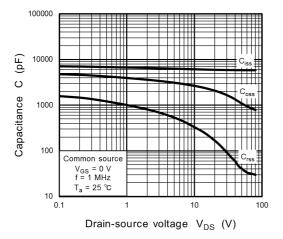


Fig. 8.11 Capacitance - V_{DS}

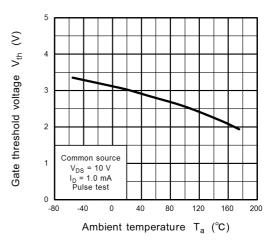


Fig. 8.8 V_{th} - T_a

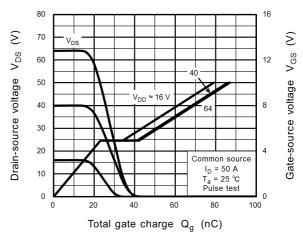


Fig. 8.10 Dynamic Input/Output Characteristics

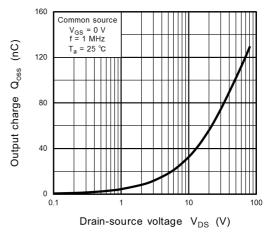


Fig. 8.12 Qoss - VDS



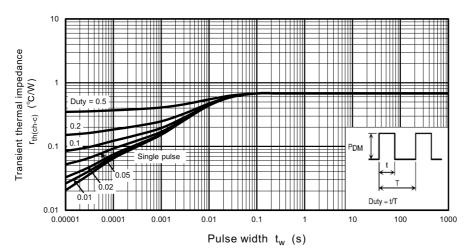


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

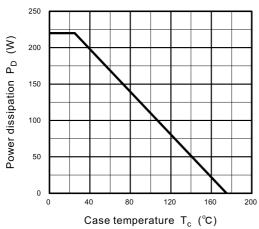


Fig. 8.14 P_D - T_c (Guaranteed Maximum)

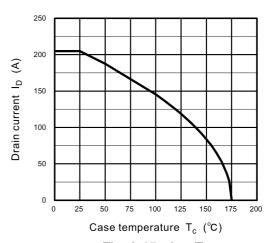


Fig. 8.15 $I_D - T_c$

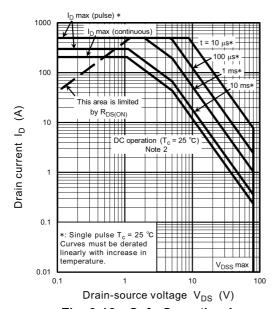


Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

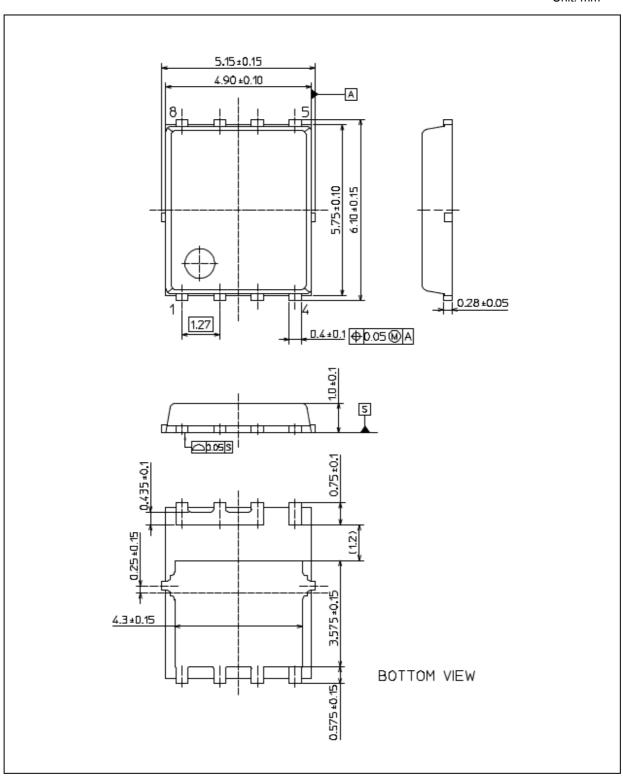
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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Package Dimensions

Unit: mm



Weight: 0.121 g (typ.)

Package Name(s)
TOSHIBA: 2-6L1A
Nickname: SOP Advance(E)



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